

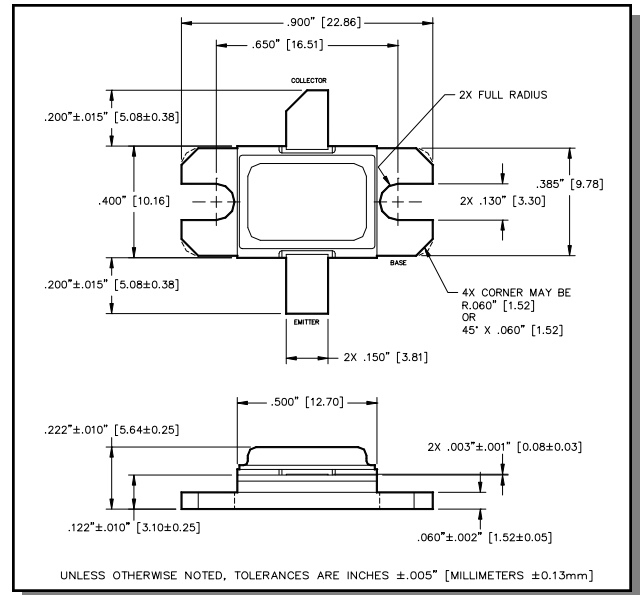
Avionics Pulsed Power Transistor  
350W, 1025-1150 MHz, 10µs Pulse, 1% Duty

M/A-COM Products  
Released, 14 Sep 2007

## Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS Compliant

## Outline Drawing



## Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	65	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Collector Current (Peak)	$I_C$	25	A
Power Dissipation @ +25°C	$P_{TOT}$	1.1	kW
Storage Temperature	$T_{STG}$	-65 to +200	°C
Junction Temperature	$T_J$	200	°C

## Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (Room Ambient )

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	$I_C = 250\text{mA}$		$BV_{CES}$	65	-	V
Collector-Emitter Leakage Current	$V_{CE} = 50\text{V}$		$I_{CES}$	-	15	mA
Thermal Resistance	$V_{CC} = 50\text{V}$ , $P_{out} = 350\text{W}$	$F = 1090\text{ MHz}$	$R_{TH(JC)}$	-	0.16	°C/W
Input Power	$V_{CC} = 50\text{V}$ , $P_{out} = 350\text{W}$	$F = 1090\text{ MHz}$	$P_{IN}$	-	44	W
Power Gain	$V_{CC} = 50\text{V}$ , $P_{out} = 350\text{W}$	$F = 1090\text{ MHz}$	$G_P$	9.0	-	dB
Collector Efficiency	$V_{CC} = 50\text{V}$ , $P_{out} = 350\text{W}$	$F = 1090\text{ MHz}$	$\eta_C$	45	-	%
Input Return Loss	$V_{CC} = 50\text{V}$ , $P_{out} = 350\text{W}$	$F = 1090\text{ MHz}$	RL	-	-9	dB
Load Mismatch Tolerance	$V_{CC} = 50\text{V}$ , $P_{out} = 350\text{W}$	$F = 1090\text{ MHz}$	VSWR-T	-	10:1	-
Load Mismatch Stability	$V_{CC} = 50\text{V}$ , $P_{out} = 350\text{W}$	$F = 1090\text{ MHz}$	VSWR-S	-	1.5:1	-

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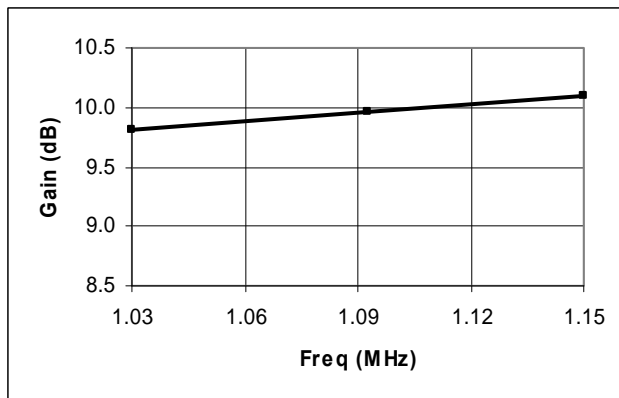
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## Typical Broadband RF Performance

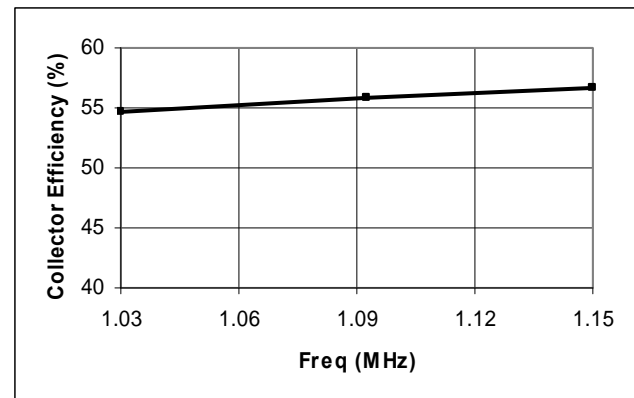
(Provided for information only - 100% Production testing performed at 1090MHz only)

Freq. (MHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (10:1)
1025	37	350	9.81	12.8	54.6	-14.8	S	P
1090	35	350	9.96	12.5	55.8	-16.7	S	P
1150	34	350	10.10	12.4	56.6	-26.1	S	P

## Gain vs. Frequency

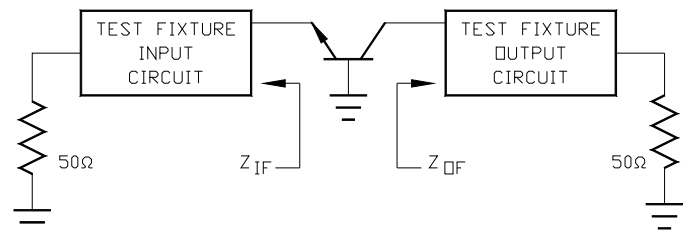


## Collector Efficiency vs. Frequency



## RF Test Fixture Impedance

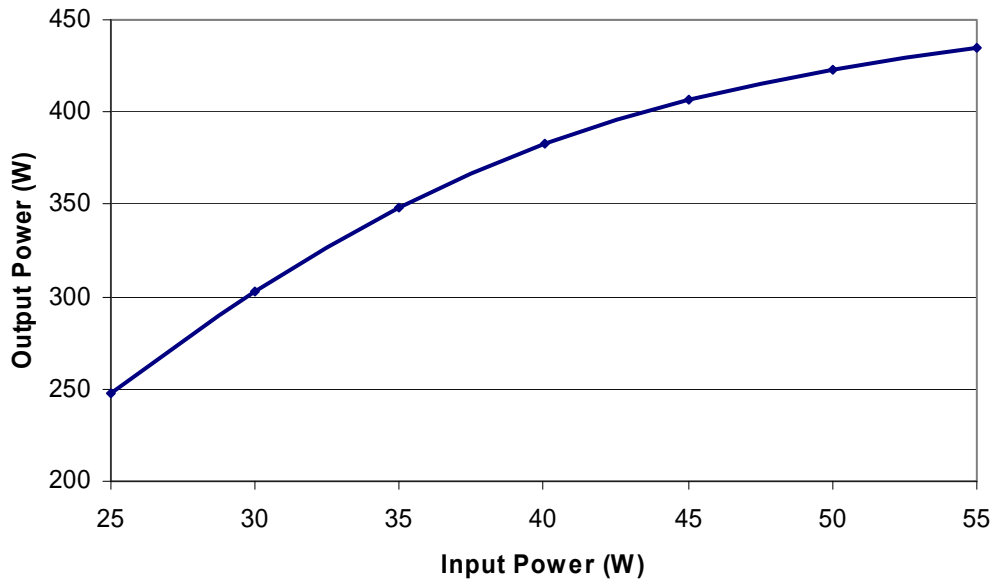
F (MHz)	Z <sub>IF</sub> (Ω)	Z <sub>OF</sub> (Ω)
960	1.8 - j3.7	2.2 - j2.8
1025	1.8 - j3.2	2.3 - j2.2
1090	1.8 - j2.7	2.4 - j1.7
1150	1.9 - j2.3	2.6 - j1.5
1215	2.0 - j1.9	2.8 - j1.3



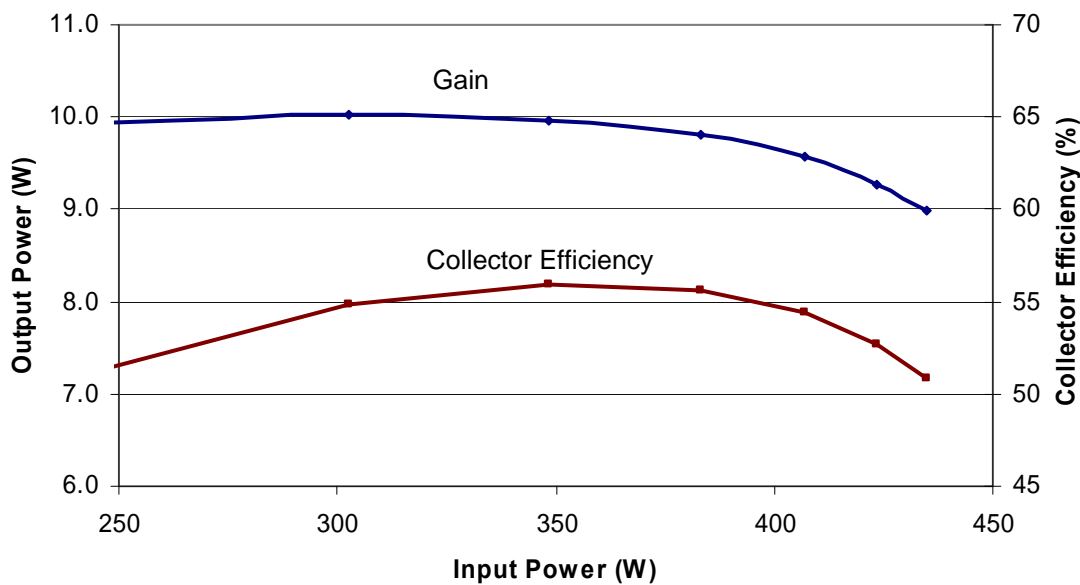
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## RF Power Transfer Curve 1090 MHz, Output Power vs. Input Power



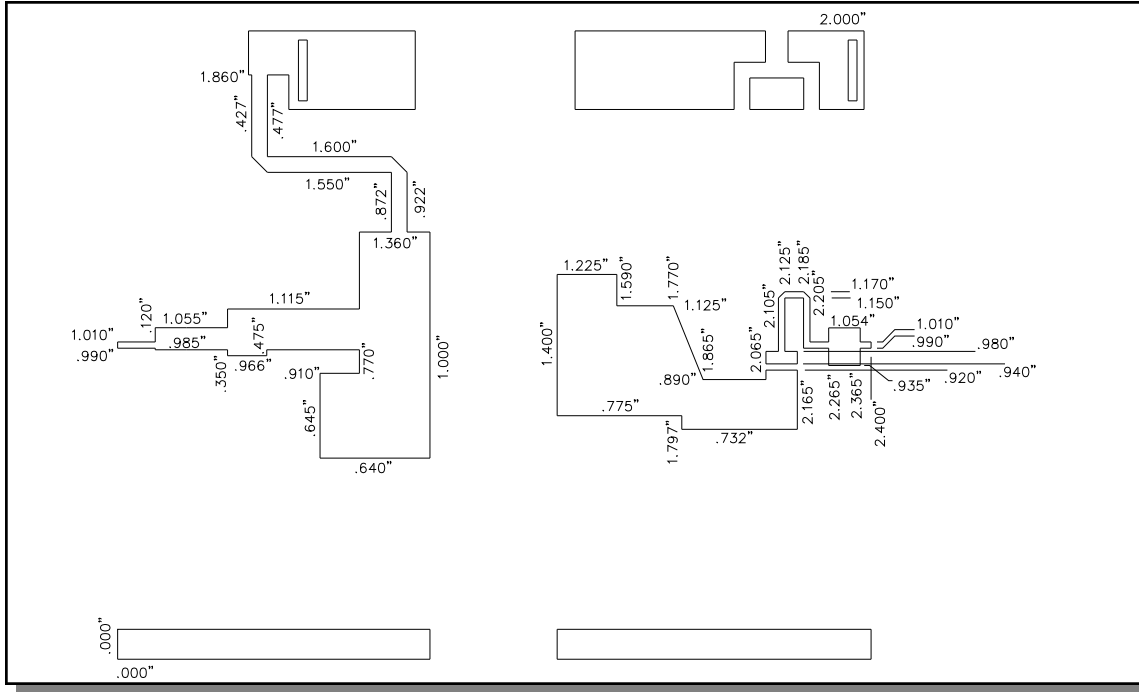
## RF Power Transfer Curve 1090 MHz, Gain & Efficiency vs. Output Power



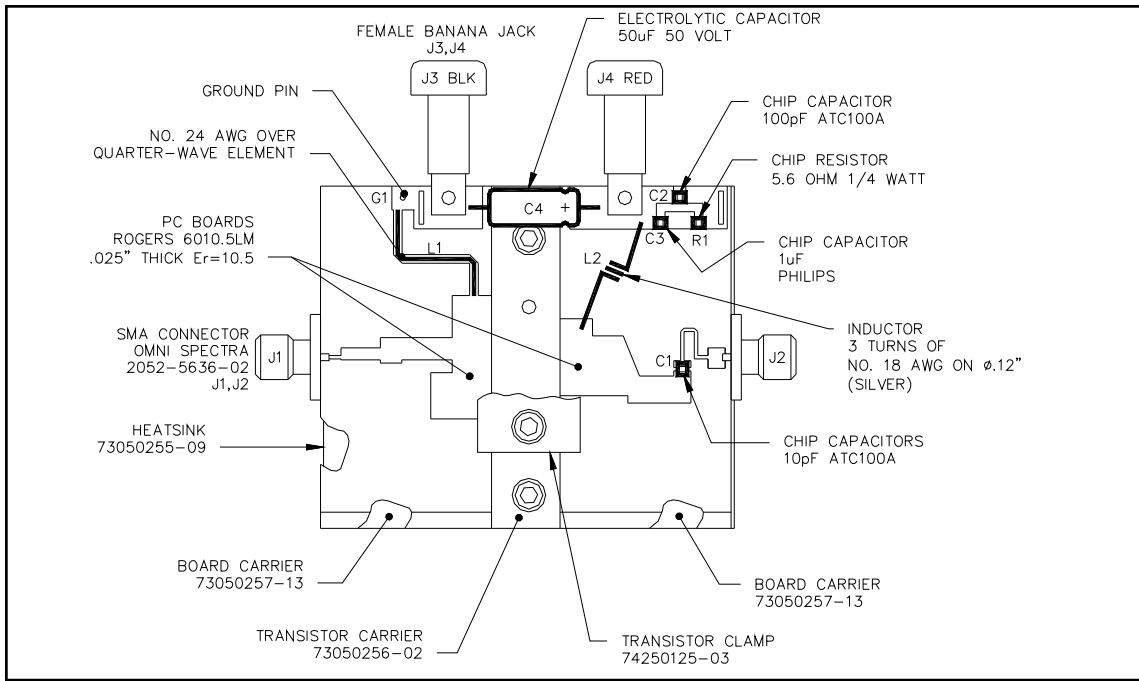
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## Test Fixture Circuit Dimensions



## Test Fixture Assembly



**ADVANCED:** Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.  
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